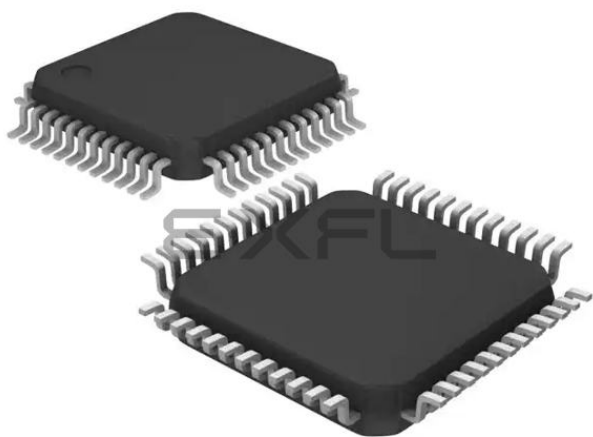




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"[Embedded - Microcontrollers](#)" refer to small, integrated circuits designed to perform specific tasks within larger systems. These microcontrollers are essentially compact computers on a single chip, containing a processor core, memory, and programmable input/output peripherals. They are called "embedded" because they are embedded within electronic devices to control various functions, rather than serving as standalone computers. Microcontrollers are crucial in modern electronics, providing the intelligence and control needed for a wide range of applications.

Applications of "[Embedded - Microcontrollers](#)"

Details

Product Status	Obsolete
Core Processor	STM8A
Core Size	8-Bit
Speed	24MHz
Connectivity	CANbus, I ² C, LINbus, SPI, UART/USART
Peripherals	Brown-out Detect/Reset, POR, PWM, WDT
Number of I/O	38
Program Memory Size	64KB (64K x 8)
Program Memory Type	FLASH
EEPROM Size	2K x 8
RAM Size	6K x 8
Voltage - Supply (Vcc/Vdd)	3V ~ 5.5V
Data Converters	A/D 10x10b
Oscillator Type	Internal
Operating Temperature	-40°C ~ 150°C (TA)
Mounting Type	Surface Mount
Package / Case	48-LQFP
Supplier Device Package	48-LQFP (7x7)
Purchase URL	https://www.e-xfl.com/product-detail/stmicroelectronics/stm8af5288tdx

Contents

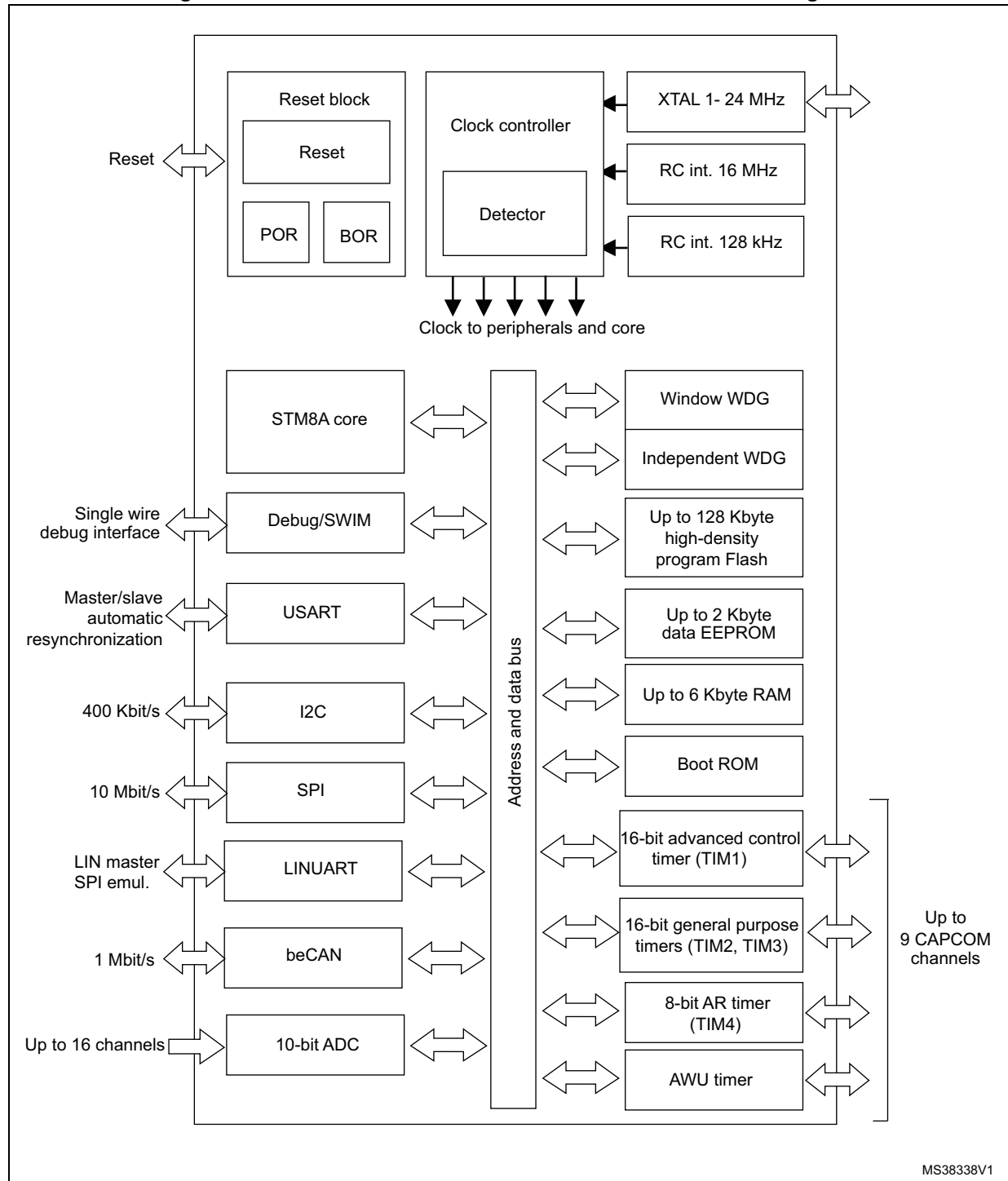
1	Introduction	9
2	Description	10
3	Product line-up	11
4	Block diagram	12
5	Product overview	14
5.1	STM8A central processing unit (CPU)	14
5.1.1	Architecture and registers	14
5.1.2	Addressing	14
5.1.3	Instruction set	14
5.2	Single wire interface module (SWIM) and debug module (DM)	15
5.2.1	SWIM	15
5.2.2	Debug module	15
5.3	Interrupt controller	15
5.4	Flash program and data EEPROM	15
5.4.1	Architecture	15
5.4.2	Write protection (WP)	16
5.4.3	Protection of user boot code (UBC)	16
5.4.4	Read-out protection (ROP)	16
5.5	Clock controller	17
5.5.1	Features	17
5.5.2	16 MHz high-speed internal RC oscillator (HSI)	17
5.5.3	128 kHz low-speed internal RC oscillator (LSI)	18
5.5.4	24 MHz high-speed external crystal oscillator (HSE)	18
5.5.5	External clock input	18
5.5.6	Clock security system (CSS)	18
5.6	Low-power operating modes	19
5.7	Timers	20
5.7.1	Watchdog timers	20
5.7.2	Auto-wakeup counter	20
5.7.3	Beeper	20

List of figures

Figure 1.	STM8AF526x/8x/Ax and STM8AF6269/8x/Ax block diagram	12
Figure 2.	Flash memory organization of STM8A products.	16
Figure 3.	LQFP 80-pin pinout.	28
Figure 4.	LQFP 64-pin pinout.	29
Figure 5.	LQFP 48-pin pinout.	30
Figure 6.	STM8AF62xx LQFP/VFQFPN 32-pin pinout	31
Figure 7.	STM8AF52x6 VFQFPN32 32-pin pinout	32
Figure 8.	Register and memory map	40
Figure 9.	Pin loading conditions.	59
Figure 10.	Pin input voltage	60
Figure 11.	fCPU _{max} versus V _{DD}	62
Figure 12.	External capacitor C _{EXT}	63
Figure 13.	Typ. I _{DD(RUN)HSE} vs. V _{DD} @ f _{CPU} = 16 MHz, peripherals = on	67
Figure 14.	Typ. I _{DD(RUN)HSE} vs. f _{CPU} @ V _{DD} = 5.0 V, peripherals = on	67
Figure 15.	Typ. I _{DD(RUN)HSI} vs. V _{DD} @ f _{CPU} = 16 MHz, peripherals = off	67
Figure 16.	Typ. I _{DD(WFI)HSE} vs. V _{DD} @ f _{CPU} = 16 MHz, peripherals = on	67
Figure 17.	Typ. I _{DD(WFI)HSE} vs. f _{CPU} @ V _{DD} = 5.0 V, peripherals = on	67
Figure 18.	Typ. I _{DD(WFI)HSI} vs. V _{DD} @ f _{CPU} = 16 MHz, peripherals = off	67
Figure 19.	HSE external clock source	68
Figure 20.	HSE oscillator circuit diagram.	69
Figure 21.	Typical HSI frequency vs V _{DD} .	70
Figure 22.	Typical LSI frequency vs V _{DD} .	71
Figure 23.	Typical V _{IL} and V _{IH} vs V _{DD} @ four temperatures	75
Figure 24.	Typical pull-up resistance R _{PU} vs V _{DD} @ four temperatures	75
Figure 25.	Typical pull-up current I _{pu} vs V _{DD} @ four temperatures ⁽¹⁾	76
Figure 26.	Typ. V _{OL} @ V _{DD} = 3.3 V (standard ports).	76
Figure 27.	Typ. V _{OL} @ V _{DD} = 5.0 V (standard ports).	76
Figure 28.	Typ. V _{OL} @ V _{DD} = 3.3 V (true open drain ports)	76
Figure 29.	Typ. V _{OL} @ V _{DD} = 5.0 V (true open drain ports)	76
Figure 30.	Typ. V _{OL} @ V _{DD} = 3.3 V (high sink ports)	77
Figure 31.	Typ. V _{OL} @ V _{DD} = 5.0 V (high sink ports)	77
Figure 32.	Typ. V _{DD} - V _{OH} @ V _{DD} = 3.3 V (standard ports).	77
Figure 33.	Typ. V _{DD} - V _{OH} @ V _{DD} = 5.0 V (standard ports).	77
Figure 34.	Typ. V _{DD} - V _{OH} @ V _{DD} = 3.3 V (high sink ports)	77
Figure 35.	Typ. V _{DD} - V _{OH} @ V _{DD} = 5.0 V (high sink ports)	77
Figure 36.	Typical NRST V _{IL} and V _{IH} vs V _{DD} @ four temperatures	78
Figure 37.	Typical NRST pull-up resistance R _{PU} vs V _{DD} .	79
Figure 38.	Typical NRST pull-up current I _{pu} vs V _{DD}	79
Figure 39.	Recommended reset pin protection	80
Figure 40.	SPI timing diagram in slave mode and with CPHA = 0.	82
Figure 41.	SPI timing diagram in slave mode and with CPHA = 1.	82
Figure 42.	SPI timing diagram - master mode	83
Figure 43.	Typical application with ADC	85
Figure 44.	ADC accuracy characteristics.	86
Figure 45.	LQFP80 - 80-pin, 14 x 14 mm low-profile quad flat package outline	90
Figure 46.	LQFP80 - 80-pin, 14 x 14 mm low-profile quad flat package recommended footprint.	92
Figure 47.	LQFP80 marking example (package top view).	93

4 Block diagram

Figure 1. STM8AF526x/8x/Ax and STM8AF6269/8x/Ax block diagram



Detailed feature list:

- Full duplex, asynchronous communications
- NRZ standard format (mark/space)
- High-precision baud rate generator system
 - Common programmable transmit and receive baud rates up to $f_{\text{MASTER}}/16$
- Programmable data word length (8 or 9 bits)
- Configurable stop bits: Support for 1 or 2 stop bits
- LIN master mode:
 - LIN break and delimiter generation
 - LIN break and delimiter detection with separate flag and interrupt source for readback checking.
- Transmitter clock output for synchronous communication
- Separate enable bits for transmitter and receiver
- Transfer detection flags:
 - Receive buffer full
 - Transmit buffer empty
 - End of transmission flags
- Parity control:
 - Transmits parity bit
 - Checks parity of received data byte
- Four error detection flags:
 - Overrun error
 - Noise error
 - Frame error
 - Parity error
- Six interrupt sources with flags:
 - Transmit data register empty
 - Transmission complete
 - Receive data register full
 - Idle line received
 - Parity error
 - LIN break and delimiter detection
- Two interrupt vectors:
 - Transmitter interrupt
 - Receiver interrupt
- Reduced power consumption mode
- Wakeup from mute mode (by idle line detection or address mark detection)
- Two receiver wakeup modes:
 - Address bit (MSB)
 - Idle line

Table 11. STM8AF526x/8x/Ax and STM8AF6269/8x/Ax pin description

Pin number					Pin name	Type	Input				Output			Main function (after reset)	Default alternate function	Alternate function after remap [option bit]
LQFP80	LQFP64	LQFP48	STM8AF62xx LQFP32/VFQFPN32	STM8AF52xx6 VFQFPN32			Floating	Wpu	Ext. interrupt	High sink	Speed	OD	PP			
1	1	1	1	1	NRST	I/O	-	X	-	-	-	-	-	Reset		-
2	2	2	2	2	PA1/OSCIN ⁽¹⁾	I/O	X	X	-	-	O1	X	X	Port A1	Resonator/crystal in	-
3	3	3	3	3	PA2/OSCOOUT	I/O	X	X	X	-	O1	X	X	Port A2	Resonator/crystal out	-
4	4	4	-	-	V _{SSIO_1}	S	-	-	-	-	-	-	-	I/O ground		-
5	5	5	4	4	V _{SS}	S	-	-	-	-	-	-	-	Digital ground		-
6	6	6	5	5	VCAP	S	-	-	-	-	-	-	-	1.8 V regulator capacitor		-
7	7	7	6	6	V _{DD}	S	-	-	-	-	-	-	-	Digital power supply		-
8	8	8	7	7	V _{DDIO_1}	S	-	-	-	-	-	-	-	I/O power supply		-
9	9	9	-	-	PA3/TIM2_CH3	I/O	X	X	X	-	O1	X	X	Port A3	Timer 2 - channel 3	TIM3_CH1 [AFR1]
10	10	10	-	-	PA4/USART_RX	I/O	X	X	X	-	O3	X	X	Port A4	USART receive	-
11	11	11	-	-	PA5/USART_TX	I/O	X	X	X	-	O3	X	X	Port A5	USART transmit	-
12	12	12	-	8	PA6/USART_CK ⁽²⁾	I/O	X	X	X	-	O3	X	X	Port A6	USART synchro nous clock	-
13	-	-	-	-	PH0	I/O	X	X	-	HS	O3	X	X	Port H0	-	-
14	-	-	-	-	PH1	I/O	X	X	-	HS	O3	X	X	Port H1	-	-
15	-	-	-	-	PH2	I/O	X	X	-	-	O1	X	X	Port H2	-	-
16	-	-	-	-	PH3	I/O	X	X	-	-	O1	X	X	Port H3	-	-
17	13	-	-	-	PF7/AIN15	I/O	X	X	-	-	O1	X	X	Port F7	Analog input 15	-
18	14	-	-	-	PF6/AIN14	I/O	X	X	-	-	O1	X	X	Port F6	Analog input 14	-
19	15	-	-	-	PF5/AIN13	I/O	X	X	-	-	O1	X	X	Port F5	Analog input 13	-
20	16	-	8	-	PF4/AIN12	I/O	X	X	-	-	O1	X	X	Port F4	Analog input 12	-
21	17	-	-	-	PF3/AIN11	I/O	X	X	-	-	O1	X	X	Port F3	Analog input 11	-

Table 13. I/O port hardware register map (continued)

Address	Block	Register label	Register name	Reset status
0x00 5014	Port E	PE_ODR	Port E data output latch register	0x00
0x00 5015		PE_IDR	Port E input pin value register	0xXX ⁽¹⁾
0x00 5016		PE_DDR	Port E data direction register	0x00
0x00 5017		PE_CR1	Port E control register 1	0x00
0x00 5018		PE_CR2	Port E control register 2	0x00
0x00 5019	Port F	PF_ODR	Port F data output latch register	0x00
0x00 501A		PF_IDR	Port F input pin value register	0xXX ⁽¹⁾
0x00 501B		PF_DDR	Port F data direction register	0x00
0x00 501C		PF_CR1	Port F control register 1	0x00
0x00 501D		PF_CR2	Port F control register 2	0x00
0x00 501E	Port G	PG_ODR	Port G data output latch register	0x00
0x00 501F		PG_IDR	Port G input pin value register	0xXX ⁽¹⁾
0x00 5020		PG_DDR	Port G data direction register	0x00
0x00 5021		PG_CR1	Port G control register 1	0x00
0x00 5022		PG_CR2	Port G control register 2	0x00
0x00 5023	Port H	PH_ODR	Port H data output latch register	0x00
0x00 5024		PH_IDR	Port H input pin value register	0xXX ⁽¹⁾
0x00 5025		PH_DDR	Port H data direction register	0x00
0x00 5026		PH_CR1	Port H control register 1	0x00
0x00 5027		PH_CR2	Port H control register 2	0x00
0x00 5028	Port I	PI_ODR	Port I data output latch register	0x00
0x00 5029		PI_IDR	Port I input pin value register	0xXX ⁽¹⁾
0x00 502A		PI_DDR	Port I data direction register	0x00
0x00 502B		PI_CR1	Port I control register 1	0x00
0x00 502C		PI_CR2	Port I control register 2	0x00

1. Depends on the external circuitry.

Table 19. Option byte description (continued)

Option byte no.	Description
OPT3	LSI_EN: Low speed internal clock enable 0: LSI clock is not available as CPU clock source 1: LSI clock is available as CPU clock source
	IWDG_HW: Independent watchdog 0: IWDG Independent watchdog activated by software 1: IWDG Independent watchdog activated by hardware
	WWDG_HW: Window watchdog activation 0: WWDG window watchdog activated by software 1: WWDG window watchdog activated by hardware
	WWDG_HALT: Window watchdog reset on Halt 0: No reset generated on Halt if WWDG active 1: Reset generated on Halt if WWDG active
OPT4	EXTCLK: External clock selection 0: External crystal connected to OSCIN/OSCOU 1: External clock signal on OSCIN
	CKAWUSEL: Auto-wakeup unit/clock 0: LSI clock source selected for AWU 1: HSE clock with prescaler selected as clock source for AWU
	PRSC[1:0]: AWU clock prescaler 00: 24 MHz to 128 kHz prescaler 01: 16 MHz to 128 kHz prescaler 10: 8 MHz to 128 kHz prescaler 11: 4 MHz to 128 kHz prescaler
OPT5	HSECNT[7:0]: HSE crystal oscillator stabilization time This configures the stabilization time to 0.5, 8, 128, and 2048 HSE cycles with corresponding option byte values of 0xE1, 0xD2, 0xB4, and 0x00.
OPT6	TMU[3:0]: Enable temporary memory unprotection 0101: TMU disabled (permanent ROP). Any other value: TMU enabled.
OPT7	WAIT STATE: Wait state configuration This option configures the number of wait states inserted when reading from the Flash/data EEPROM memory. 0: No wait state 1: One wait state
OPT8	TMU_KEY 1 [7:0]: Temporary unprotection key 0 Temporary unprotection key: Must be different from 0x00 or 0xFF
OPT9	TMU_KEY 2 [7:0]: Temporary unprotection key 1 Temporary unprotection key: Must be different from 0x00 or 0xFF
OPT10	TMU_KEY 3 [7:0]: Temporary unprotection key 2 Temporary unprotection key: Must be different from 0x00 or 0xFF
OPT11	TMU_KEY 4 [7:0]: Temporary unprotection key 3 Temporary unprotection key: Must be different from 0x00 or 0xFF

10 Electrical characteristics

10.1 Parameter conditions

Unless otherwise specified, all voltages are referred to V_{SS} .

10.1.1 Minimum and maximum values

Unless otherwise specified the minimum and maximum values are guaranteed in the worst conditions of ambient temperature, supply voltage and frequencies by tests in production on 100% of the devices with an ambient temperature at $T_A = -40\text{ }^{\circ}\text{C}$, $T_A = 25\text{ }^{\circ}\text{C}$, and $T_A = T_{Amax}$ (given by the selected temperature range).

Data based on characterization results, design simulation and/or technology characteristics are indicated in the table footnotes and are not tested in production.

10.1.2 Typical values

Unless otherwise specified, typical data are based on $T_A = 25\text{ }^{\circ}\text{C}$, $V_{DD} = 5.0\text{ V}$. They are given only as design guidelines and are not tested.

Typical ADC accuracy values are determined by characterization of a batch of samples from a standard diffusion lot over the full temperature range.

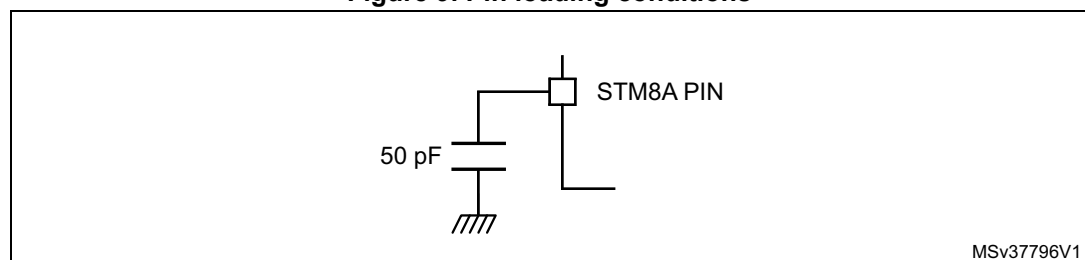
10.1.3 Typical curves

Unless otherwise specified, all typical curves are given only as design guidelines and are not tested.

10.1.4 Loading capacitor

The loading conditions used for pin parameter measurement are shown in [Figure 9](#).

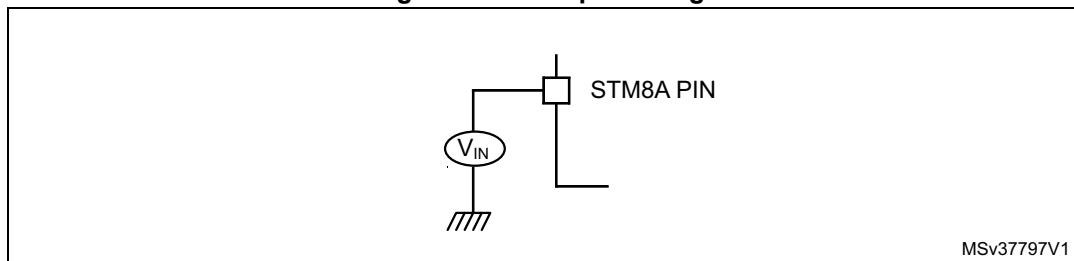
Figure 9. Pin loading conditions



10.1.5 Pin input voltage

The input voltage measurement on a pin of the device is described in [Figure 10](#).

Figure 10. Pin input voltage



10.2 Absolute maximum ratings

Stresses above the absolute maximum ratings listed in [Table 20: Voltage characteristics](#), [Table 21: Current characteristics](#) and [Table 22: Thermal characteristics](#) may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these conditions is not implied. Exposure to maximum rating conditions for extended periods may affect the device's reliability. The device's mission profile (application conditions) is compliant with the JEDEC JESD47 qualification standard, extended mission profiles are available on demand.

Table 20. Voltage characteristics

Symbol	Ratings	Min	Max	Unit
V _{DDx} - V _{SS}	Supply voltage (including V _{DDA} and V _{DDIO}) ⁽¹⁾	-0.3	6.5	V
V _{IN}	Input voltage on true open drain pins (PE1, PE2) ⁽²⁾	V _{SS} - 0.3	6.5	
	Input voltage on any other pin ⁽²⁾	V _{SS} - 0.3	V _{DD} + 0.3	
V _{DDx} - V _{DD}	Variations between different power pins	-	50	mV
V _{SSx} - V _{SS}	Variations between all the different ground pins	-	50	
V _{ESD}	Electrostatic discharge voltage	see <i>Absolute maximum ratings (electrical sensitivity) on page 88</i>		

1. All power (V_{DD} , V_{DDIO} , V_{DDA}) and ground (V_{SS} , V_{SSIO} , V_{SSA}) pins must always be connected to the external power supply
2. $I_{INJ(PIN)}$ must never be exceeded. This is implicitly insured if V_{IN} maximum is respected. If V_{IN} maximum cannot be respected, the injection current must be limited externally to the $I_{INJ(PIN)}$ value. A positive injection is induced by $V_{IN} > V_{DD}$ while a negative injection is induced by $V_{IN} < V_{SS}$. For true open-drain pads, there is no positive injection current, and the corresponding V_{IN} maximum must always be respected

10.3 Operating conditions

Table 24. General operating conditions

Symbol	Parameter	Conditions	Min	Max	Unit
f_{CPU}	Internal CPU clock frequency	1 wait state $T_A = -40\text{ }^{\circ}\text{C to } 150\text{ }^{\circ}\text{C}$	16	24	MHz
		0 wait state $T_A = -40\text{ }^{\circ}\text{C to } 150\text{ }^{\circ}\text{C}$	0	16	
$V_{\text{DD}}/V_{\text{DDIO}}$	Standard operating voltage	-	3.0	5.5	V
$V_{\text{CAP}}^{(1)}$	C_{EXT} : capacitance of external capacitor	-	470	3300	nF
	ESR of external capacitor	at 1 MHz ⁽²⁾	-	0.3	Ω
	ESL of external capacitor		-	15	nH
T_A	Ambient temperature	Suffix A	- 40	85	$^{\circ}\text{C}$
		Suffix C		125	
		Suffix D		150	
T_J	Junction temperature range	Suffix A	- 40	90	
		Suffix C		130	
		Suffix D		155	

- Care should be taken when selecting the capacitor, due to its tolerance, as well as the parameter dependency on temperature, DC bias and frequency in addition to other factors. The parameter maximum value must be respected for the full application range.
- This frequency of 1 MHz as a condition for V_{CAP} parameters is given by design of internal regulator.

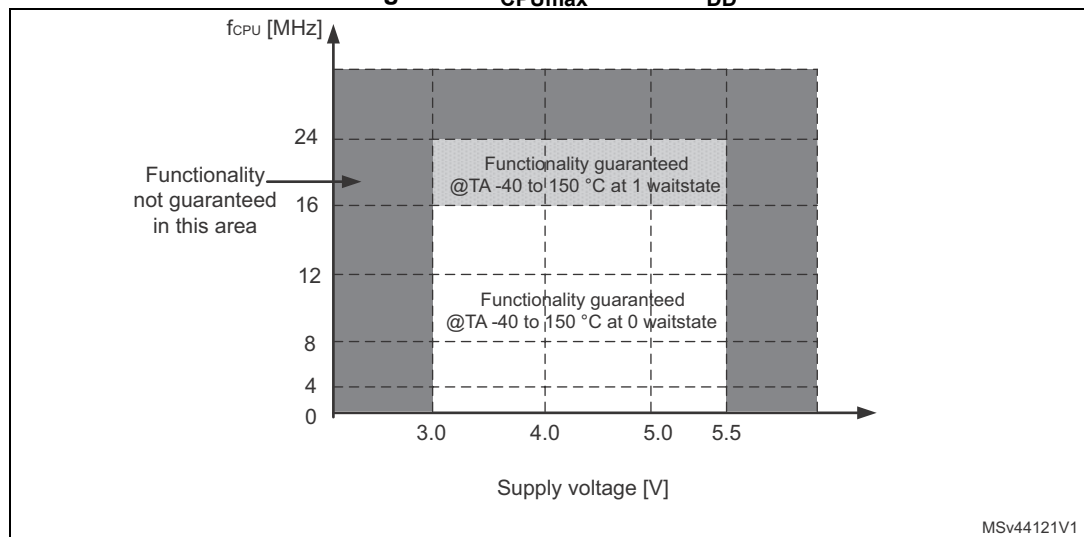
Figure 11. f_{CPUmax} versus V_{DD} 

Table 26. Total current consumption in Run, Wait and Slow mode. General conditions for V_{DD} apply, $T_A = -40\text{ }^{\circ}\text{C}$ to $150\text{ }^{\circ}\text{C}$

Symbol	Parameter	Conditions	Typ	Max	Unit
$I_{DD(RUN)}^{(1)}$	Supply current in Run mode	All peripherals clocked, code executed from Flash program memory, HSE external clock (without resonator)	$f_{CPU} = 24\text{ MHz}$ 1 ws	8.7	16.8 ⁽²⁾
			$f_{CPU} = 16\text{ MHz}$	7.4	14
			$f_{CPU} = 8\text{ MHz}$	4.0	7.4 ⁽²⁾
			$f_{CPU} = 4\text{ MHz}$	2.4	4.1 ⁽²⁾
			$f_{CPU} = 2\text{ MHz}$	1.5	2.5
$I_{DD(RUN)}^{(1)}$	Supply current in Run mode	All peripherals clocked, code executed from RAM, HSE external clock (without resonator)	$f_{CPU} = 24\text{ MHz}$	4.4	6.0 ⁽²⁾
			$f_{CPU} = 16\text{ MHz}$	3.7	5.0
			$f_{CPU} = 8\text{ MHz}$	2.2	3.0 ⁽²⁾
			$f_{CPU} = 4\text{ MHz}$	1.4	2.0 ⁽²⁾
			$f_{CPU} = 2\text{ MHz}$	1.0	1.5
$I_{DD(WFI)}^{(1)}$	Supply current in Wait mode	CPU stopped, all peripherals off, HSE external clock	$f_{CPU} = 24\text{ MHz}$	2.4	3.1 ⁽²⁾
			$f_{CPU} = 16\text{ MHz}$	1.65	2.5
			$f_{CPU} = 8\text{ MHz}$	1.15	1.9 ⁽²⁾
			$f_{CPU} = 4\text{ MHz}$	0.90	1.6 ⁽²⁾
			$f_{CPU} = 2\text{ MHz}$	0.80	1.5
$I_{DD(SLOW)}^{(1)}$	Supply current in Slow mode	f_{CPU} scaled down, all peripherals off, code executed from RAM	External clock 16 MHz $f_{CPU} = 125\text{ kHz}$	1.50	1.95
			LSI internal RC $f_{CPU} = 128\text{ kHz}$	1.50	1.80 ⁽²⁾

1. The current due to I/O utilization is not taken into account in these values.
2. Guaranteed by design, not tested in production.

10.3.5 Memory characteristics

Flash program memory/data EEPROM memory

General conditions: $T_A = -40\text{ }^{\circ}\text{C}$ to $150\text{ }^{\circ}\text{C}$.

Table 35. Flash program memory/data EEPROM memory

Symbol	Parameter	Conditions	Min ⁽¹⁾	Typ	Max	Unit
V_{DD}	Operating voltage (all modes, execution/write/erase)	f_{CPU} is 16 to 24 MHz with 1 ws f_{CPU} is 0 to 16 MHz with 0 ws	3.0	-	5.5	V
V_{DD}	Operating voltage (code execution)	f_{CPU} is 16 to 24 MHz with 1 ws f_{CPU} is 0 to 16 MHz with 0 ws	2.6	-	5.5	
t_{prog}	Standard programming time (including erase) for byte/word/block (1 byte/4 bytes/128 bytes)	-	-	6	6.6	ms
	Fast programming time for 1 block (128 bytes)	-	-	3	3.3	
t_{erase}	Erase time for 1 block (128 bytes)	-	-	3	3.3	

1. Guaranteed by characterization results, not tested in production.

Table 36. Flash program memory

Symbol	Parameter	Condition	Min	Max	Unit
T_{WE}	Temperature for writing and erasing	-	-40	150	$^{\circ}\text{C}$
N_{WE}	Flash program memory endurance (erase/write cycles) ⁽¹⁾	$T_A = 25\text{ }^{\circ}\text{C}$	1000	-	cycles
t_{RET}	Data retention time	$T_A = 25\text{ }^{\circ}\text{C}$	40	-	years
		$T_A = 55\text{ }^{\circ}\text{C}$	20	-	

1. The physical granularity of the memory is four bytes, so cycling is performed on four bytes even when a write/erase operation addresses a single byte.

10.3.7 Reset pin characteristics

Subject to general operating conditions for V_{DD} and T_A unless otherwise specified.

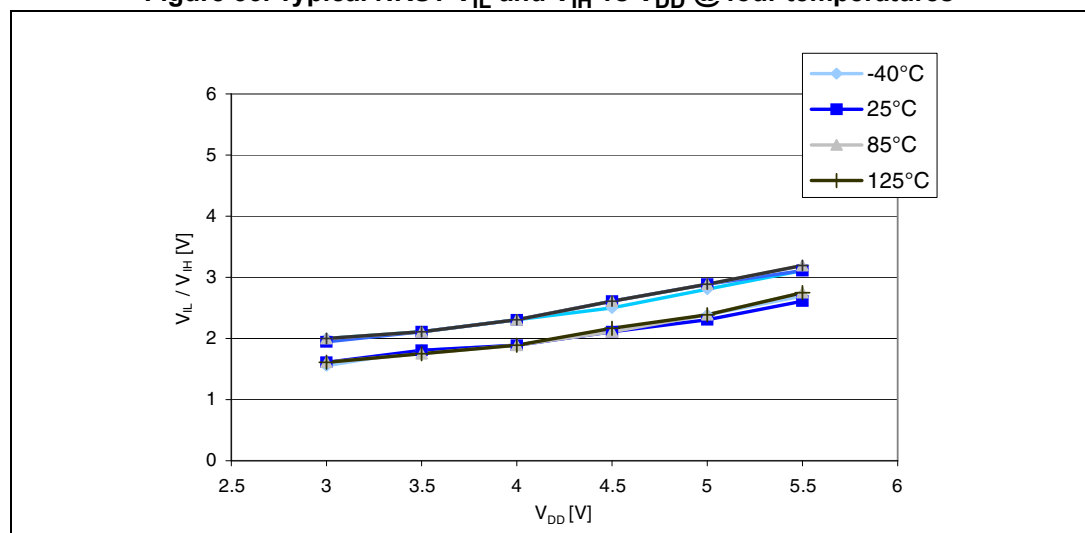
Table 39. NRST pin characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$V_{IL(NRST)}$	NRST low-level input voltage ⁽¹⁾	-	V_{SS}	-	$0.3 \times V_{DD}$	V
$V_{IH(NRST)}$	NRST high-level input voltage ⁽¹⁾	-	$0.7 \times V_{DD}$	-	V_{DD}	
$V_{OL(NRST)}$	NRST low-level output voltage ⁽¹⁾	$I_{OL} = 3 \text{ mA}$	-	-	0.6	
$R_{PU(NRST)}$	NRST pull-up resistor	-	30	40	60	k Ω
t_{IFP}	NRST input filtered pulse ⁽¹⁾	-	85	-	315	ns
$t_{INFP(NRST)}$	NRST Input not filtered pulse duration ⁽²⁾	-	500	-	-	

1. Guaranteed by characterization results, not tested in production.

2. Guaranteed by design, not tested in production.

Figure 36. Typical NRST V_{IL} and V_{IH} vs V_{DD} @ four temperatures



10.3.10 I²C interface characteristicsTable 42. I²C characteristics

Symbol	Parameter	Standard mode I ² C		Fast mode I ² C ⁽¹⁾		Unit
		Min ⁽²⁾	Max ⁽²⁾	Min ⁽²⁾	Max ⁽²⁾	
t _{w(SCLL)}	SCL clock low time	4.7	-	1.3	-	μs
t _{w(SCLH)}	SCL clock high time	4.0	-	0.6	-	
t _{su(SDA)}	SDA setup time	250	-	100	-	ns
t _{h(SDA)}	SDA data hold time	0 ⁽³⁾	-	0 ⁽⁴⁾	900 ⁽³⁾	
t _{r(SDA)} t _{r(SCL)}	SDA and SCL rise time (V _{DD} 3 V to 5.5 V)	-	1000	-	300	
t _{f(SDA)} t _{f(SCL)}	SDA and SCL fall time (V _{DD} 3 V to 5.5 V)	-	300	-	300	
t _{h(STA)}	START condition hold time	4.0	-	0.6	-	μs
t _{su(STA)}	Repeated START condition setup time	4.7	-	0.6	-	
t _{su(STO)}	STOP condition setup time	4.0	-	0.6	-	μs
t _{w(STO:STA)}	STOP to START condition time (bus free)	4.7	-	1.3	-	μs
C _b	Capacitive load for each bus line	-	400	-	400	pF

1. f_{MASTER} must be at least 8 MHz to achieve max fast I²C speed (400 kHz)
2. Data based on standard I²C protocol requirement, not tested in production
3. The maximum hold time of the start condition has only to be met if the interface does not stretch the low time
4. The device must internally provide a hold time of at least 300 ns for the SDA signal in order to bridge the undefined region of the falling edge of SCL

10.3.12 EMC characteristics

Susceptibility tests are performed on a sample basis during product characterization.

Functional EMS (electromagnetic susceptibility)

While executing a simple application (toggling 2 LEDs through I/O ports), the product is stressed by two electromagnetic events until a failure occurs (indicated by the LEDs).

- **ESD:** Electrostatic discharge (positive and negative) is applied on all pins of the device until a functional disturbance occurs. This test conforms with the IEC 1000-4-2 standard.
- **FTB:** A burst of fast transient voltage (positive and negative) is applied to V_{DD} and V_{SS} through a 100 pF capacitor, until a functional disturbance occurs. This test conforms with the IEC 1000-4-4 standard.

A device reset allows normal operations to be resumed. The test results are given in the table below based on the EMS levels and classes defined in application note AN1709.

Designing hardened software to avoid noise problems

EMC characterization and optimization are performed at component level with a typical application environment and simplified MCU software. It should be noted that good EMC performance is highly dependent on the user application and the software in particular.

Therefore it is recommended that the user applies EMC software optimization and prequalification tests in relation with the EMC level requested for his application.

Software recommendations

The software flowchart must include the management of runaway conditions such as:

- Corrupted program counter
- Unexpected reset
- Critical data corruption (control registers...)

Prequalification trials

Most of the common failures (unexpected reset and program counter corruption) can be recovered by applying a low state on the NRST pin or the oscillator pins for 1 second.

To complete these trials, ESD stress can be applied directly on the device, over the range of specification values. When unexpected behavior is detected, the software can be hardened to prevent unrecoverable errors occurring (see application note AN1015).

Table 45. EMS data

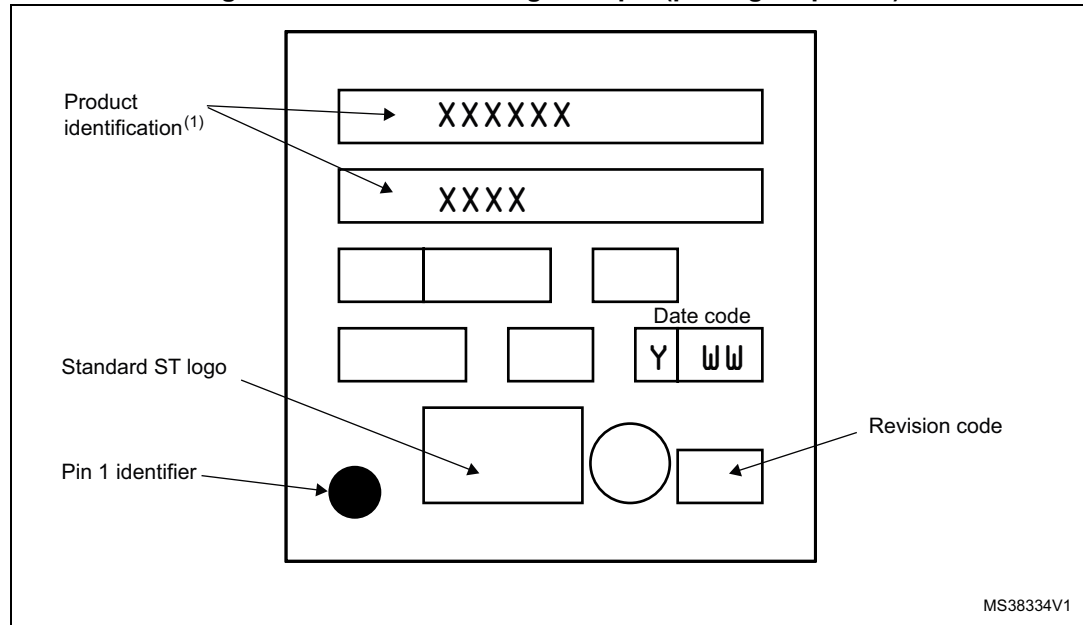
Symbol	Parameter	Conditions	Level/class
V_{FESD}	Voltage limits to be applied on any I/O pin to induce a functional disturbance	$V_{DD} = 3.3\text{ V}$, $T_A = 25\text{ }^{\circ}\text{C}$, $f_{MASTER} = 16\text{ MHz}$ (HSI clock), Conforms to IEC 1000-4-2	3/B
V_{EFTB}	Fast transient voltage burst limits to be applied through 100 pF on V_{DD} and V_{SS} pins to induce a functional disturbance	$V_{DD} = 3.3\text{ V}$, $T_A = 25\text{ }^{\circ}\text{C}$, $f_{MASTER} = 16\text{ MHz}$ (HSI clock), Conforms to IEC 1000-4-4	4/A

Device marking

The following figure gives an example of topside marking orientation versus pin 1 identifier location.

Other optional marking or inset/upset marks, which identify the parts throughout supply chain operations, are not indicated below.

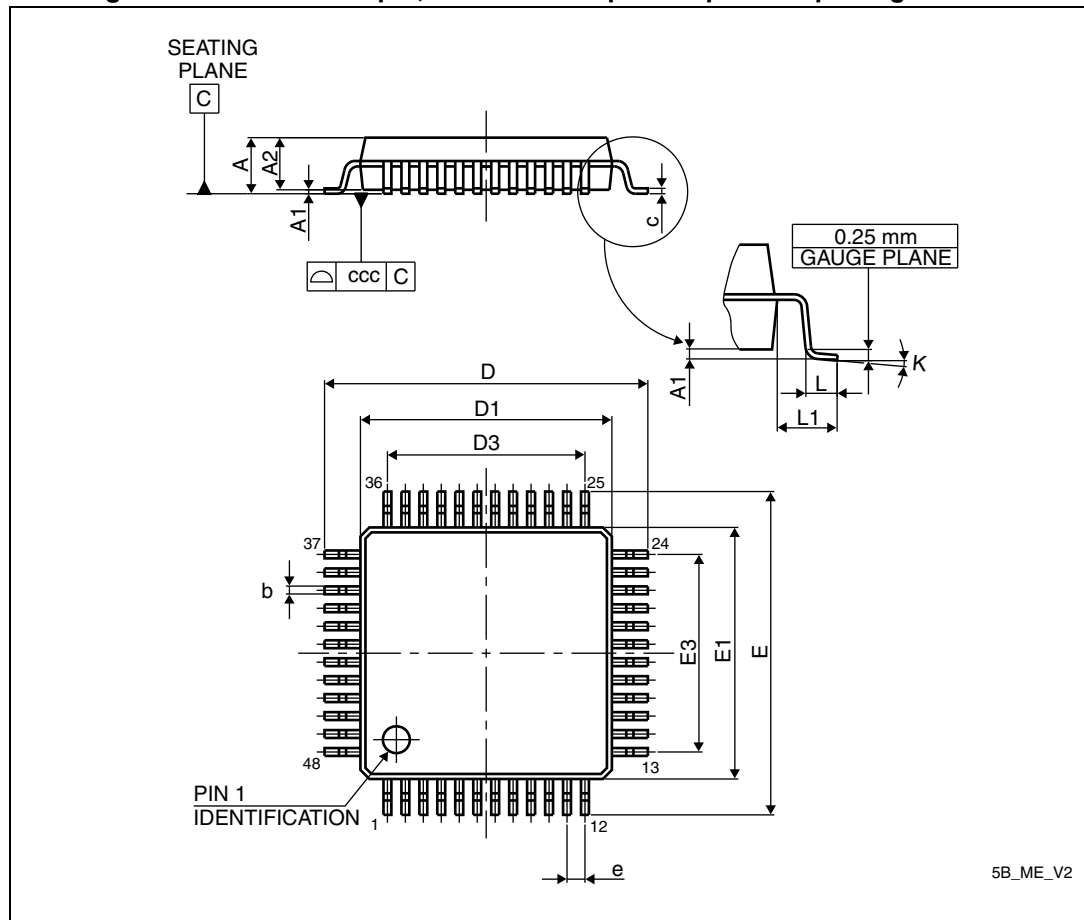
Figure 50. LQFP64 marking example (package top view)



1. Parts marked as "ES", "E" or accompanied by an Engineering Sample notification letter are not yet qualified and therefore not approved for use in production. ST is not responsible for any consequences resulting from such use. In no event will ST be liable for the customer using any of these engineering samples in production. ST's quality department must be contacted to run a qualification activity prior to any decision to use these engineering samples.

11.3 LQFP48 package information

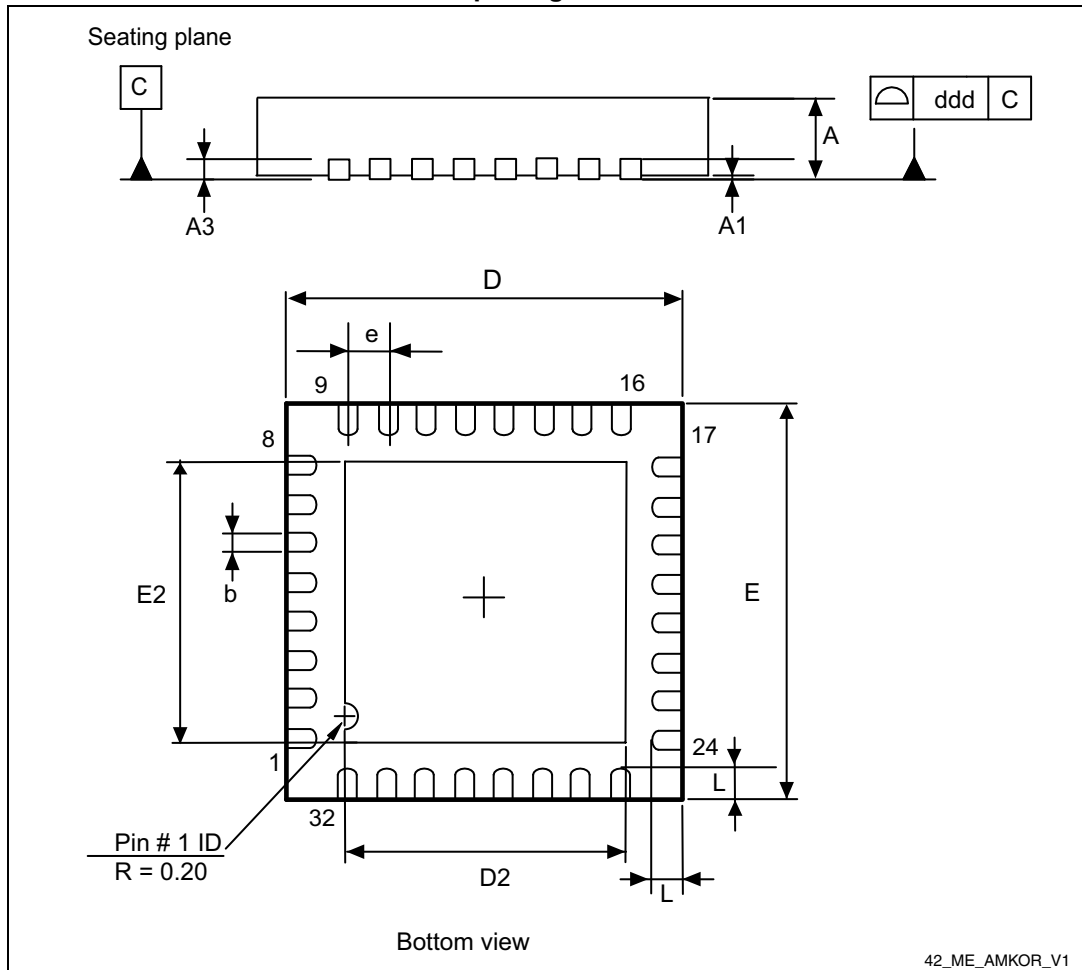
Figure 51. LQFP48 - 48-pin, 7 x 7 mm low-profile quad flat package outline



1. Drawing is not to scale.

11.5 VFQFPN32 package information

Figure 57. VFQFPN32 - 32-pin, 5x5 mm, 0.5 mm pitch very thin profile fine pitch quad flat package outline



1. Drawing is not to scale.

Table 55. Document revision history (continued)

Date	Revision	Changes
22-Aug-2008	2 (continued)	Table 18: Typ. IDD(WFI)HSI vs. VDD @ fCPU = 16 MHz, peripherals = off: Replaced the source blocks 'simple USART', 'very low-end timer (timer 4)', and 'EEPROM' with 'LINUART', 'timer4' and 'reserved' respectively, added TMU registers. Table 20: HSE oscillator circuit diagram: Updated OPT6 and NOPT6, added OPT7 to 17 (TMU, BL) Table 21: Typical HSI frequency vs VDD: Updated OPT1 UBC[7:0], OPT4 CKAUSEL, OPT4 PRSC [1:0], and OPT6, added OPT7 to 16 (TMU). Table 23: Operating lifetime: Amended footnotes. Table 26: Total current consumption in Run, Wait and Slow mode. General conditions for VDD apply, TA = -40 °C to 150 °C: Added parameter 'voltage and current operating conditions'. Table 27: Total current consumption in Halt and Active-halt modes. General conditions for VDD applied. TA = -40 °C to 55 °C unless otherwise stated: Amended footnotes. Table 28: Oscillator current consumption: Replaced. Table 29: Programming current consumption: Amended maximum data and footnotes. Table 21: Current characteristics: Replaced. Table 22: Thermal characteristics: Added and amended IDD(RUN) data; amended IDD(WFI) data; amended footnotes. Table 32: HSE oscillator characteristics: Filled in, amended maximum data and footnotes. Figure 13 to Figure 18: info on peripheral activity added. Table 33: HSI oscillator characteristics: Modified fHSE_ext data and added VHSEdhl data. Table 35: Flash program memory/data EEPROM memory: Removed ACC_HSI parameters and replaced with ACC_HS parameters; amended data and footnotes. Amended data of 'RAM and hardware registers' table. Table 37: Data memory: Updated names and data of N_{RW} and t_{RET} parameters. Table 40: TIM 1, 2, 3, and 4 electrical specifications: Added V_{OH} and V_{OL} parameters; Updated I_{lkg ana} parameter. Removed: Output driving current (standard ports), Output driving current (true open drain ports), and Output driving current (high sink ports). Table 46: EMI data: Updated f_{ADC}, t_S, and t_{CONV} data. Table: ADC accuracy for VDDA = 3.3 V: removed the 4-MHz condition from all parameters. Table 47: ESD absolute maximum ratings: Removed the 4-MHz condition from all parameters; updated footnote 1 and removed footnote 2. Table 51: LQFP48 - 48-pin, 7 x 7 mm low-profile quad flat package mechanical data: Added data for T_A = 145 °C. Figure 53: Updated memory size, pin count and package type information.

Table 55. Document revision history (continued)

Date	Revision	Changes
18-Jul-2012	9 (continued)	Table 26: Total current consumption in Run, Wait and Slow mode. General conditions for VDD apply, TA = -40 °C to 150 °C: updated conditions for I_{DD(RUN)}. Table 38: I/O static characteristics: added new condition and new max values for rise and fall time; updated footnote 2. Section 10.3.7: Reset pin characteristics: updated text below Figure 38: Typical NRST pull-up current I_{pu} vs VDD Figure 39: Recommended reset pin protection: updated unit of capacitor. Table 41: SPI characteristics: updated SCK high and low time conditions and values. Figure 42: SPI timing diagram - master mode: replaced 'SCK input' signals with 'SCK output' signals. Updated Table 49: LQFP80 - 80-pin, 14 x 14 mm low-profile quad flat package mechanical data, Table 50: LQFP64 - 64-pin, 10 x 10 mm low-profile quad flat package mechanical data, Table 51: LQFP48 - 48-pin, 7 x 7 mm low-profile quad flat package mechanical data, Table 52: LQFP32 - 32-pin, 7 x 7 mm low-profile quad flat package mechanical data, Table 53: VFQFPN32 - 32-pin, 5 x 5 mm, 0.5 mm pitch very thin profile fine pitch quad flat package mechanical data Replaced Figure 48: LQFP64 - 64-pin, 10 x 10 mm low-profile quad flat package outline, Figure 51: LQFP48 - 48-pin, 7 x 7 mm low-profile quad flat package outline and Figure 54: LQFP32 - 32-pin, 7 x 7 mm low-profile quad flat package outline Added Figure 49: LQFP64 - 64-pin, 10 x 10 mm low-profile quad flat package recommended footprint, Figure 52: LQFP48 - 48-pin, 7 x 7 mm low-profile quad flat package recommended footprint and Figure 55: LQFP32 - 32-pin, 7 x 7 mm low-profile quad flat package recommended footprint Updated Figure 57: VFQFPN32 - 32-pin, 5x5 mm, 0.5 mm pitch very thin profile fine pitch quad flat package outline Updated Figure 60: STM8AF526x/8x/Ax and STM8AF6269/8x/Ax ordering information scheme¹ Section 13.2.2: C and assembly toolchains: added www.iar.com.
31-Mar-2014	10	Updated: – Table 1: Device summary, – Table: STM8AF52xx product line-up with CAN, – Table: STM8AF/H/P51xx product line-up with CAN, – Table: STM8AF/H/P61xx product line-up without CAN, – Table 11: STM8AF526x/8x/Ax and STM8AF6269/8x/Ax pin description, – The maximum speed in Section 5.9.3: Serial peripheral interface (SPI), – t_{TEMP} Reset release delay /VDD rising typical and max values in Table 25: Operating conditions at power-up/power-down, – The symbol t_{IFP(NRST)} with t_{INFP(NRST)} in Table 39: NRST pin characteristics, – The address and comment for Reset in Table 17: STM8A interrupt table.